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## Structural defects and non-ferroelectric piezoelectricity in an unpoled SrTiO<sub>3</sub>-Bi<sub>12</sub>TiO<sub>20</sub> (ST-BT) composite ceramics

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Anomalous piezoelectricity  $SrTiO_3-Bi_{12}TiO_{20}$  (ST-BT) composite ceramics fabricated by traditional sintering technology were first studied by positron annihilation lifetime spectroscopy and Doppler broadening spectroscopy. A large number of crystal defects were observed in ST-BT composite ceramics with the sintering temperature below 980 °C. The piezoelectric effect appeared concurrently with a high concentration of single-vacancy defects in the ceramics, suggesting that it may be closely related to the microstructure. This further proves that the flexoelectric effect is the origin of non-ferroelectric piezoelectricity. © 2012 Published by Elsevier Ltd. on behalf of Acta Materialia Inc.

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Non-ferroelectric piezoelectric materials are promising for high-temperature applications due to their lack of a Curie temperature. These non-ferroelectric piezoelectric materials, including Langasite single crystals, oriented AlN films and polar glass ceramics, have been studied in detail in recent decades [1–5], but they are extremely expensive for their complex production processes. Recently, the traditional sintering technology for non-ferroelectric piezoelectric ceramics has been improved a lot. Zhao et al. [6,7] reported unusual piezoelectricity in Na<sub>0.5</sub>Bi<sub>0.5</sub>TiO<sub>3</sub>-based and (Na<sub>0.5</sub>Bi<sub>0.5</sub>)<sub>0.94-</sub> Ba<sub>0.06</sub>TiO<sub>3</sub>-Bi<sub>12</sub>TiO<sub>20</sub> composite ceramics that had been produced by the ordinary sintering technique. A piezoelectric CaCu<sub>3</sub>Ti<sub>4</sub>O<sub>12</sub> ceramic material was also reported by Tararam et al. [8]. Now a new type of naturally polarized non-ferroelectric piezoelectric SrTiO<sub>3</sub>-Bi<sub>12</sub>TiO<sub>20</sub> (ST-BT) composite ceramic has been prepared by the conventional solid-state reaction route at Shandong University. This material shows great potential for high-temperature piezoelectric applications.

The actual mechanism of piezoelectricity in nonferroelectric ceramics that are fabricated by traditional sintering technology is not yet clear. However, the flexoelectric effect is widely accepted as explaining the origin of piezoelectricity [6–12]. The flexoelectric effect, which occurs in the insulating oxides, is the coupling between the mechanical strain gradient and electric polarization induced by inhomogeneous strain in the materials. A strain gradient can be formed in a crystalline structure by lattice mismatch [13–15], impurities [16] or chemical fluctuation in cationic segregation [17]. All of these factors lead to a great number of crystal defects (vacancies, divacancies, interstitials, etc.). In contrast to ferroelectric polarization, which occurs in the whole crystalline structure of non-centrosymmetric crystals, nonferroelectric piezoelectricity is localized in the volumes with broken symmetry that are subjected to inhomogeneous deformation [8]. If the theory that the flexoelectric effect causes non-ferroelectric piezoelectricity is correct, a high concentration of crystal defects should be found in non-ferroelectric piezoelectric ceramics. Positron annihilation spectroscopy (PAS) is well suited to the nondestructive study of structural defects in solid materials because of its sensitivity to and selectivity of crystal defects [18,19]. Many significant results have already been achieved by applying positron annihilation techniques to ceramic defect studies [20,21]. In this letter, the structural defects and piezoelectricity in nonferroelectric ST-BT composite ceramics are studied.

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We explore the correctness of attributing non-ferroelectric piezoelectricity to the flexoelectric effect.

ST–BT composite ceramics were prepared by the conventional solid-state reaction route. All the starting chemicals, Bi<sub>2</sub>O<sub>3</sub>, TiO<sub>2</sub> and SrCO<sub>3</sub>, were of analytical grade, and were mixed at the correct molar ratios to achieve ST–BT stoichiometry. These oxides were ball-milled in alcohol for 14 h, dried, pressed into disks and calcined at 800 °C for 3 h. The disks were then ground and wet-milled again under the same conditions. Subsequently, the dried powders were pressed into 15 mm diameter disks and sintered for 3 h in air at 860, 900, 940 or 980 °C (S1, S2, S3 and S4), respectively. We employed two different PAS techniques to detect the structural defects in the ST–BT composite ceramics. The piezoelectric properties were measured by an Agilent 4294A impedance analyzer and a YE2730A  $d_{33}$  meter.

Figure 1 shows the X-ray diffraction (XRD) patterns of the ST–BT composite ceramics prepared at the four different sintering temperatures. The structural analysis mainly indicates that the composite ceramics have a perovskite SrTiO<sub>3</sub> phase and a sillenite  $Bi_{12}TiO_{20}$  phase. Compared with the XRD peaks of those samples, the intensities of SrTiO<sub>3</sub> phase peaks are steady; however, the intensities of  $Bi_{12}TiO_{20}$  phase peaks change significantly. In addition, a new  $Bi_2O_3$  phase appears and the  $Bi_{12}TiO_{20}$  phase weakens when the sintering temperature rises to 980 °C. That is because the  $Bi_{12}TiO_{20}$  is decomposed at high temperature.

The PAS experiments were performed at room temperature. Two PAS techniques were employed to characterize crystal defects in the ST-BT composite ceramics, using radioactive <sup>22</sup>Na isotopes as a positron source. First, we undertook a positron lifetime spectrum experiment, the experimental details of which can be found elsewhere [18,19]. The positron lifetime spectra were measured using a fast–fast coincidence system, with a resolution of 220 ps. A  $10 \,\mu\text{Ci}^{-22}\text{Na}$  positron source was sandwiched between two identical samples. The total number of counts per spectrum was two million. Each spectrum was fitted using the LIFETIME9 [22] program run with the three-component fitting procedure. The longest lifetime  $\tau_3$  and its intensity  $I_3$  were around 2 ns and below 0.5% respectively, without significant variation for all compositions. This component is attributed to the ortho-positronium (o-Ps) annihilation in the source or at the surfaces among the grains in



**Figure 1.** XRD patterns of four ST–BT composite ceramics (S1, S2, S3 and S4). (For interpretation of the references to colour in this figure legend, the reader is referred to the web version of this article.)

the ceramics, and is ignored in the following discussion. The results of positron lifetime are presented in Table 1.  $\tau_1$  is attributed to the lifetime component of the host, which mainly reflects the structural properties of the materials. In the S4 sample, the  $\tau_1$  is higher than in the other samples. That indicates a significant change in structure, as confirmed by XRD observations.  $\tau_2$  is the defect state lifetime, which is a sensitive parameter related to the various structural defects in materials.  $I_1$ and  $I_2$  are related to intensity and reflect the concentration of the component, respectively. The average lifetime  $\tau_{\rm av} = (\tau_1 I_1 + \tau_2 I_2)/(I_1 + I_2)$  could reflect the material's microstructure. The value of  $\tau_{av}$  remains almost constantly at 232 ps at a sintering temperature below 980 °C, but this value increases sharply to 245 ps in S4. According to the two-state trapping model, the bulk lifetime  $\tau_b$  can be written as follows:  $1/\tau_b = I_1/\tau_1 + I_2/\tau_2$ . The ratio  $\tau_2/\tau_b$  can be used to identify the defect types (Table 2) [23].

Figure 2 shows the lifetime component  $\tau_2$  and its intensity  $I_2$ . Single-vacancy defects dominate in the S1, S2 and S3 samples, because the values of  $\tau_2/\tau_b$  are around 1.1 in those samples. The  $I_2$  is above 80% and the corresponding concentration of single-vacancy defects is very high. This shows that these samples have serious lattice mismatch and massive crystal defects.  $\tau_2$ is larger in the S4 sample than in the others, while the intensity falls significantly. This is because vacancy defects agglomerated and large clusters or microvoids were formed, and the interface states and micropore size increased with the generation of an impurity phase.

In order to obtain more information about which defects are associated with  $\tau_2$ , coincident Doppler broadening spectroscopy measurements were undertaken (see Fig. 3). Each spectrum collected comprised a total count of over ten million. Figure 3a shows the ratio curves of the coincident Doppler broadening spectra of samples of S1–S4, obtained by normalizing these spectra to the spectrum of Si. The ratio curve of the Si is given as a horizontal line. The shapes of these ratio curves are similar, demonstrating that the chemical environment surrounding the structural free volumes are similar. The peak width (about  $P_L = 10 \times 10^{-3} m_0 c$ ) is large, due to the superposition of positron annihilation with core electrons of different atoms.

Bringing in linear parameters, Doppler broadening is characterized by the S-parameter, which reflects the annihilation of positron–electron pairs with a lowmomentum distribution (Fig. 3b). Compared to the lifetime spectra, the S-parameter reflects the comprehensive effect of various defects. In the samples of S1–S3, the long lifetime  $\tau_2$  and its intensity  $I_2$  show no change (Fig. 2), while the S-parameter changes significantly. This indicates that the samples have a variety of single-vacancy defects. As the sintering temperature changes, the concentration of each vacancy defect changes inconsistently, but the overall performances are similar to the average lifetime. The S–W map also illustrates this point because the data cannot fall on a similar linear variation (Fig. 3c).

Figure 4a shows the piezoelectric resonance signals of the ST–BT ceramics at room temperature. The thickness direction of this plate is along the Z-axis and the Download English Version:

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